

Dual N-channel TrenchMOS logic level FET Rev. 5 — 27 December 2011

Product data sheet

1. **Product profile**

1.1 General description

Dual logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Simple gate drive required due to low gate charge

1.3 Applications

- DC-to-DC convertors
- Lithium-ion battery applications

1.4 Quick reference data

- Suitable for high frequency applications due to fast switching characteristics
- Notebook computers
- Portable equipment

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	30	V
I _D	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } Figure 1; [1] $ see Figure 3	-	-	10.4	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>	-	-	3.57	W
Static cha	racteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 8 A; T _j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	17	20	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 5 A; V _{DS} = 15 V; T _j = 25 °C; see <u>Figure 11</u>	-	3.9	-	nC

[1] Single device conducting.



Dual N-channel TrenchMOS logic level FET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	SOT96-1 (SO8)	S1 G1 S2 G2
7	D1	drain1		mbk725
8	D1	drain		

3. Ordering information

Table 3. Orderin	g information		
Type number	Package		
	Name	Description	Version
PHKD13N03LT	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

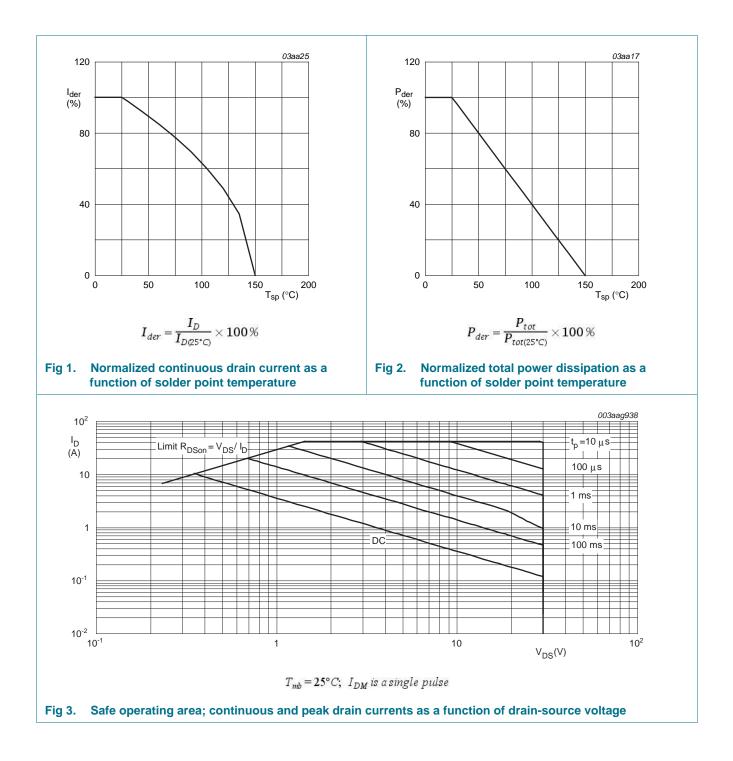
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	30	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	T_{sp} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	6.6	А
		$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	<u>[1]</u>	-	10.4	А
I _{DM}	peak drain current	$T_{sp} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s}; \text{ see } \frac{\text{Figure } 3}{10 \mu\text{s}}$	[1]	-	42	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; see <u>Figure 2</u>		-	3.57	W
T _{stg}	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
Source-drain	n diode					
I _S	source current	T _{sp} = 25 °C	[1]	-	3.2	А
I _{SM}	peak source current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \ \mu s$	<u>[1]</u>	-	42	А

[1] Single device conducting.

PHKD13N03LT Product data sheet

PHKD13N03LT

Dual N-channel TrenchMOS logic level FET

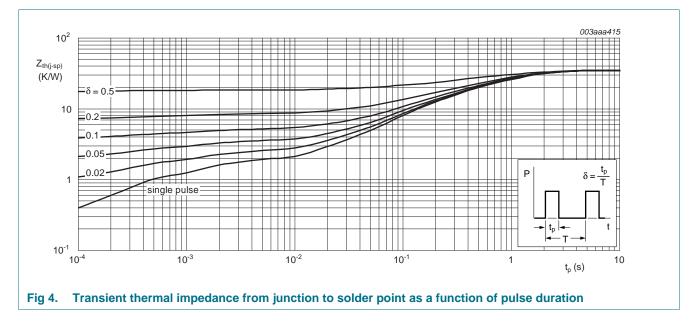


PHKD13N03LT

Dual N-channel TrenchMOS logic level FET

Thermal characteristics 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	see Figure 4	-	-	35	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	70	-	K/W



Dual N-channel TrenchMOS logic level FET

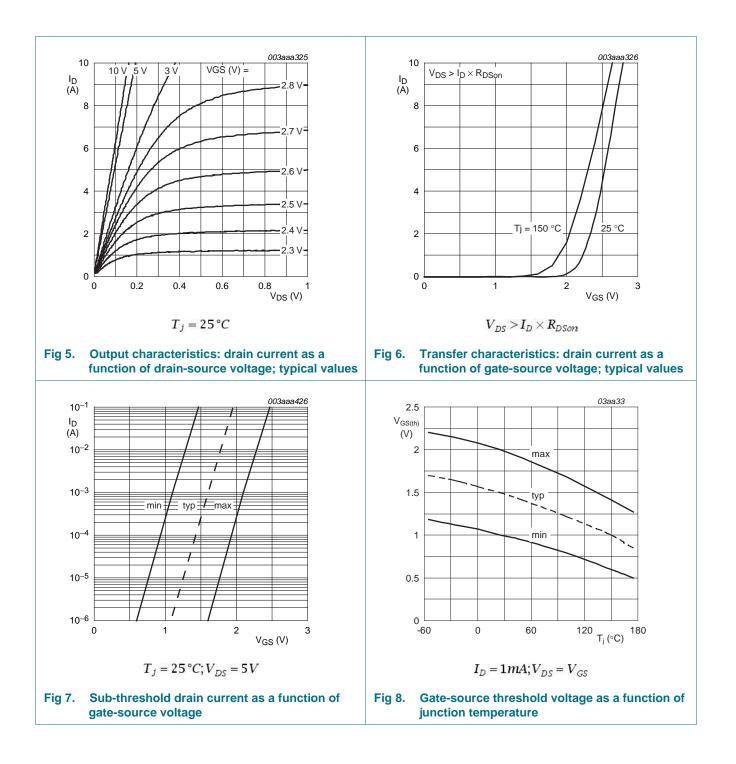
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 250 μA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 8</u>	-	-	2.2	V
		$I_D = 250 \ \mu\text{A}; V_{DS} = V_{GS}; T_j = 150 \ ^\circ\text{C};$ see <u>Figure 8</u>	0.5	-	-	V
		$I_D = 250 \ \mu\text{A}; V_{DS} = V_{GS}; T_j = 25 \ ^\circ\text{C};$ see Figure 8	1	1.5	2	V
I _{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 100 \text{ °C}$	-	-	5	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
Doon	drain-source on-state resistance	V _{GS} = 10 V; I _D = 8 A; T _j = 150 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>		34	mΩ	
		V _{GS} = 4.5 V; I _D = 7 A; T _j = 25 °C; see <u>Figure 9</u>	-	21	26	mΩ
		V_{GS} = 10 V; I_D = 8 A; T_j = 25 °C; see Figure 9; see Figure 10	-	17	20	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 5 \text{ V};$	-	10.7	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	2.7	-	nC
Q _{GD}	gate-drain charge		-	3.9	-	nC
C _{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	752	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12}$	-	200	-	pF
C _{rss}	reverse transfer capacitance		-	130	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; \text{ R}_{L} = 10 \Omega; V_{GS} = 10 \text{ V};$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \ \Omega; \ T_{j} = 25 \ ^{\circ}C; \ I_{D} = 1.5 \ A$	-	7	-	ns
t _{d(off)}	turn-off delay time		-	23	-	ns
t _f	fall time		-	11	-	ns
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 7 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 13</u>	-	0.86	1.1	V
t _{rr}	reverse recovery time	$I_S = 7 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$	-	25	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	5	-	nC

PHKD13N03LT Product data sheet

PHKD13N03LT

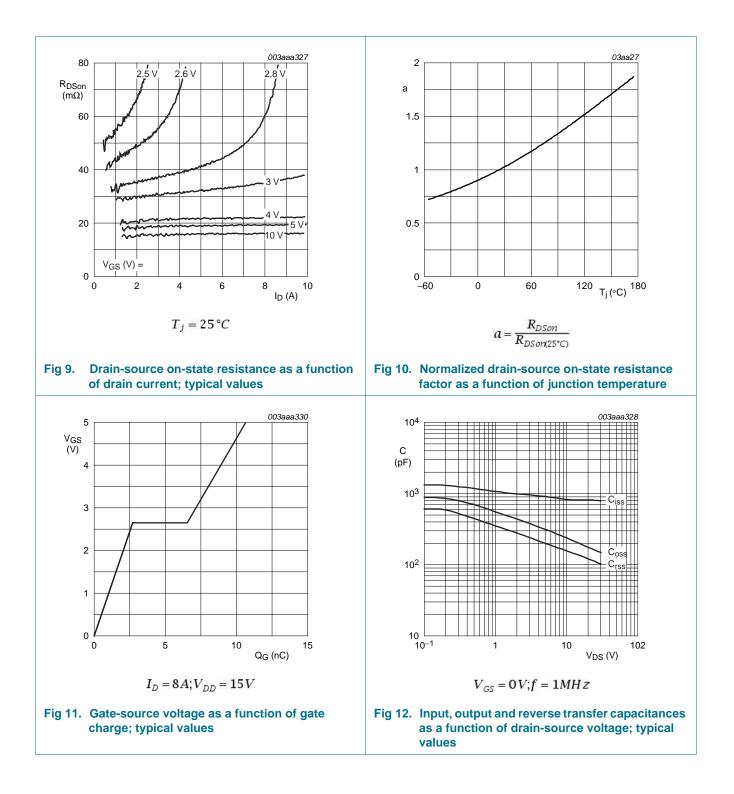
Dual N-channel TrenchMOS logic level FET



PHKD13N03LT

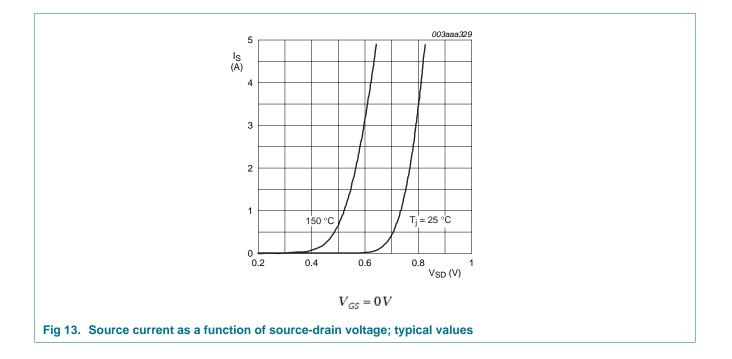
PHKD13N03LT

Dual N-channel TrenchMOS logic level FET



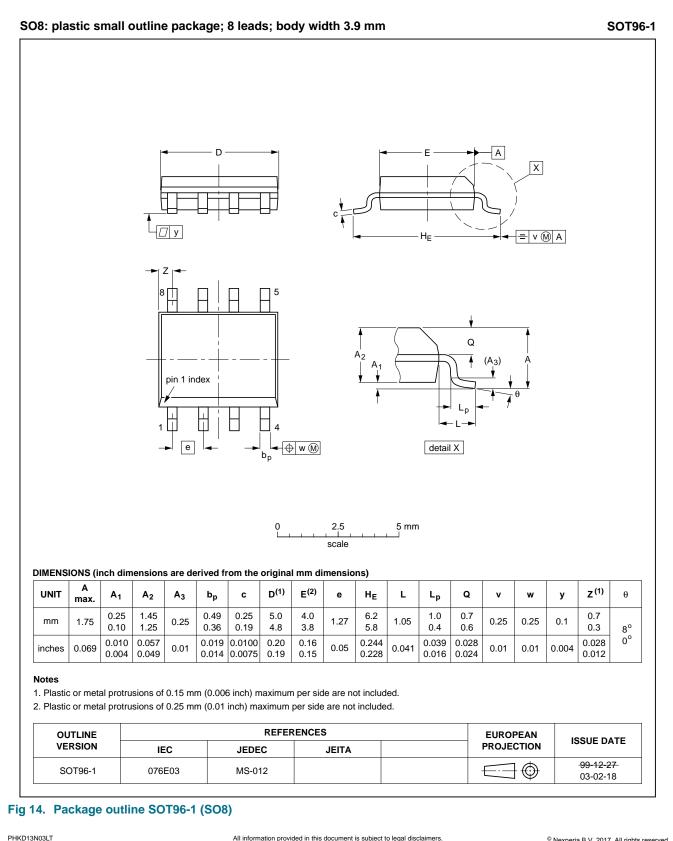
PHKD13N03LT

Dual N-channel TrenchMOS logic level FET



Dual N-channel TrenchMOS logic level FET

Package outline 7.



All information provided in this document is subject to legal disclaimers.

Dual N-channel TrenchMOS logic level FET

8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PHKD13N03LT v.5	20111227	Product data sheet	-	PHKD13N03LT v.4
Modifications:	 Various chang 	es to content.		
PHKD13N03LT v.4	20111122	Product data sheet	-	PHKD13N03LT v.3

Dual N-channel TrenchMOS logic level FET

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

9.2 Definitions

Preview — The document is a preview version only. The document is still subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and

customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

9.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — Nexperia products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using Nexperia products, and Nexperia accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the Nexperia product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using Nexperia products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). Nexperia does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Dual N-channel TrenchMOS logic level FET

Terms and conditions of commercial sale — Nexperia products are sold subject to the general terms and conditions of commercial sale, as published at <u>http://www.nexperia.com/profile/terms</u>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific Nexperia product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. Nexperia accepts no liability for inclusion and/or use of

non-automotive qualified products in automotive equipment or applications.

10. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without Nexperia's warranty of the product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond Nexperia's specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies Nexperia for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond Nexperia's standard warranty and Nexperia's product specifications.

9.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Dual N-channel TrenchMOS logic level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status11
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by NXP manufacturer:

Other Similar products are found below :

614233C 648584F IRFD120 JANTX2N5237 2N7000 FCA20N60_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2911 US6M2GTR TK10A80W,S4X(S SSM6P69NU,LF